Nanoionics-Based Switches for Radio-Frequency Applications

These switches might supplant semiconductor and MEMS switches in some applications.

John H. Glenn Research Center, Cleveland, Ohio

Nanoionics-based devices have shown promise as alternatives to microelectromechanical systems (MEMS) and semiconductor diode devices for switching radio-frequency (RF) signals in diverse systems. Examples of systems that utilize RF switches include phase shifters for electronically steerable phased-array antennas, multiplexers, cellular telephones and other radio transceivers, and other portable electronic devices.

Semiconductor diode switches can operate at low potentials (about 1 to 3 V) and high speeds (switching times of the order of nanoseconds) but are characterized by significant insertion loss, high DC power consumption, low isolation, and generation of third-order harmonics and intermodulation distortion (IMD). MEMS-based switches feature low insertion loss (of the order of 0.2 dB), low DC power consumption (picowatts), high isolation (>30 dB), and low IMD, but contain moving parts, are not highly reliable, and must be operated at high actuation potentials (20 to 60 V) generated and applied by use of complex circuitry. In addition, fabrication of MEMS is complex, involving many processing steps.

Nanoionics-based switches offer the superior RF performance and low power consumption of MEMS switches, without need for the high potentials and complex circuitry necessary for operation of MEMS switches. At the same time, nanoionics-based switches offer the high switching speed of semiconductor devices. Also, like semiconductor devices, nanoionics-based switches can be fabricated relatively inexpensively by use of conventional integrated-circuit fabrication techniques. Moreover, nanoionics-based switches have simple planar structures that can easily be integrated into RF power-distribution circuits.

Nanoionics-based switches exploit the properties of some amorphous materials (in particular, chalcogenide glasses) that can incorporate relatively large amounts of metal and behave as solid electrolytes. The ionic conductivity of such a material can be of the same order of magnitude as the electronic conductivity of a semiconductor. Under appropriate bias con-
Lunar Dust-Tolerant Electrical Connector

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An electrical connector was developed that is tolerant of the presence of lunar dust. Novel features of the connector include the use of a permeable membrane to act both as a dust barrier and as a wiper to limit the amount of dust that makes its way into the internal chamber of the connector. The development focused on the Constellation lunar extra-vehicular activity (EVA) spacesuit’s portable life support system (PLSS) battery recharge connector; however, continued research is applying this technology to other lunar surface systems such as lunar rover subsystems and cryogenic fluid transfer connections for in-situ resource utilization (ISRU) applications.

Lunar dust has been identified as a significant and present challenge in future exploration missions. In addition to posing contamination and health risks for human explorers, the inter-locking, angular nature of lunar dust and its broad grain size distribution make it particularly harmful to mechanisms with which it may come into contact. All Apollo lunar missions experienced some degree of equipment failure because of dust, and it appears that dust accumulation on exposed material is unavoidable and difficult to reverse. Both human EVA and ISRU activities are on the mission horizon and are paramount to the establishment of a permanent human base on the Moon. Reusable and dust-tolerant connection mechanisms are a critical component for mission success.

The need for dust-tolerant solutions is also seen in utility work and repair, mass transit applications, construction, mining, arctic and marine environments, diving (search and rescue), and various operations in deserts, where dust or sand clogging and coating different mechanisms and connections may render them difficult to operate or entirely inoperable.

This work was done by Jason Herman, Shazad Sadick, and Dustyn Roberts of Honeybee Robotics Spacecraft Mechanisms Corporation for Glenn Research Center.

Inquiries concerning rights for the commercial use of this invention should be addressed to NASA Glenn Research Center, Innovative Partnerships Office, Attn: Steve Fedor, Mail Stop 4–8, 21000 Brookpark Road, Cleveland, Ohio 44135. Refer to LEW-18313-1.

Compact, Reliable EEPROM Controller

This controller prevents inadvertent writes in an EEPROM.

Goddard Space Flight Center, Greenbelt, Maryland

A compact, reliable controller for an electrically erasable, programmable read-only memory (EEPROM) has been developed specifically for a space-flight application. The design may be adaptable to other applications in which there are requirements for reliability in general and, in particular, for prevention of inadvertent writing of data in EEPROM cells.

Inadvertent writes pose risks of loss of reliability in the original space-flight application and could pose such risks in other applications. Prior EEPROM controllers are large and complex and do not provide all reasonable protections (in many cases, few or no protections) against inadvertent writes. In contrast, the present controller provides several layers of protection against inadvertent writes. The controller also incorporates a write-time monitor, enabling determination of trends in the performance of an EEPROM.

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